

## Project Idea: HIGH-THROUGHPUT SCREENING CALORIMETRY

### STARTING POINT: HIGH-THROUGHPUT CALORIMETRY

Thermal microsensor with improved temporal, thermal and spatial resolution, going beyond the current capabilities on Isothermal Titration Calorimetry (ITC).

### KEY CHARACTERISTICS

**Spatial resolution & miniaturization:** micron-square size; active sensing easily deposited by sputtering.

**Temporal resolution:** up to milliseconds.

**Accurate & easy** quantification of binding rates & enthalpy changes...

**Easy adoption:** compatible with standard configuration of MicroCal.

**IPR:** EP3184981 (A1), US2017268936 (A1), CN107076622 (A), KR20170045252 (A), Japan.

### THE GOAL: HT CALORIMETRY for PHARMA

Decrease attrition rates, reducing the staggering costs of drug development.

- ✓ Accurate knowledge on **drug-target kinetics**,
- ✓ Quantitative information of a ligand binding to **several targets obtained at once**.

### CURRENT PARTNERS AND CONTACTS

- Software company for the ITC data analysis (ES).
- Experts on High Throughput Screening and pharmacology (ES).
- Clean-room microfabrication facilities (PT).

**We are looking for partners...**

- ✓ Developing instrumentation for biophysical characterization.
- ✓ With expertise in microfluidic technologies.
- ✓ End users for biophysical/biochemical characterization.

**erc** Starting point: prototype from ERC-PoC "ANTS", New technology of microthermal sensing for application in microcalorimetry.  
Principle of operation: Nernst Effect. We use a single-material device: line of permalloy 20 nm thick, 4 x 28 μm.

**Device.** We demonstrated its sensitivity for applications in microcalorimetry. The **fast response** makes it adequate for advanced microcalorimetry applications (~ milliseconds).

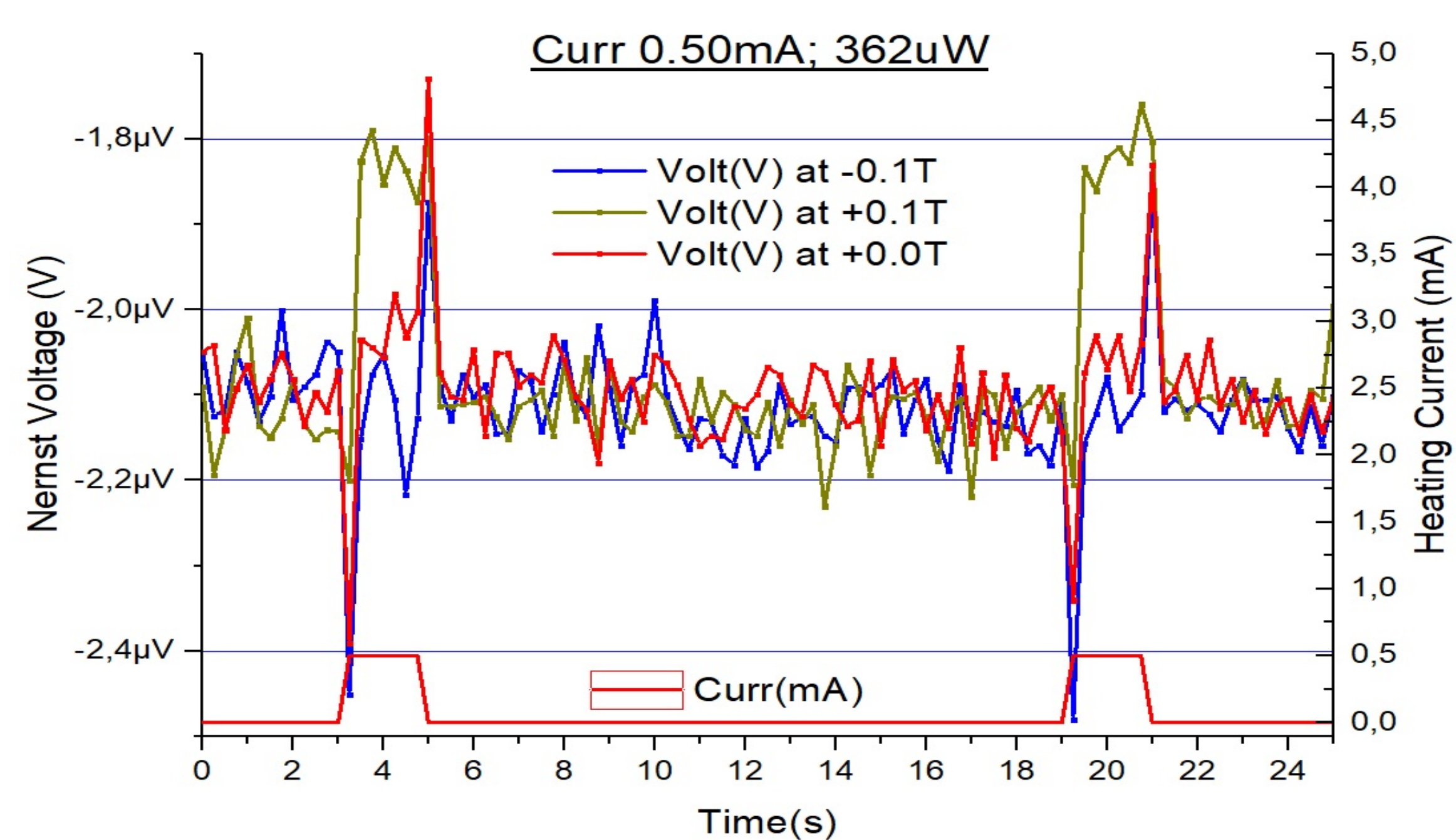
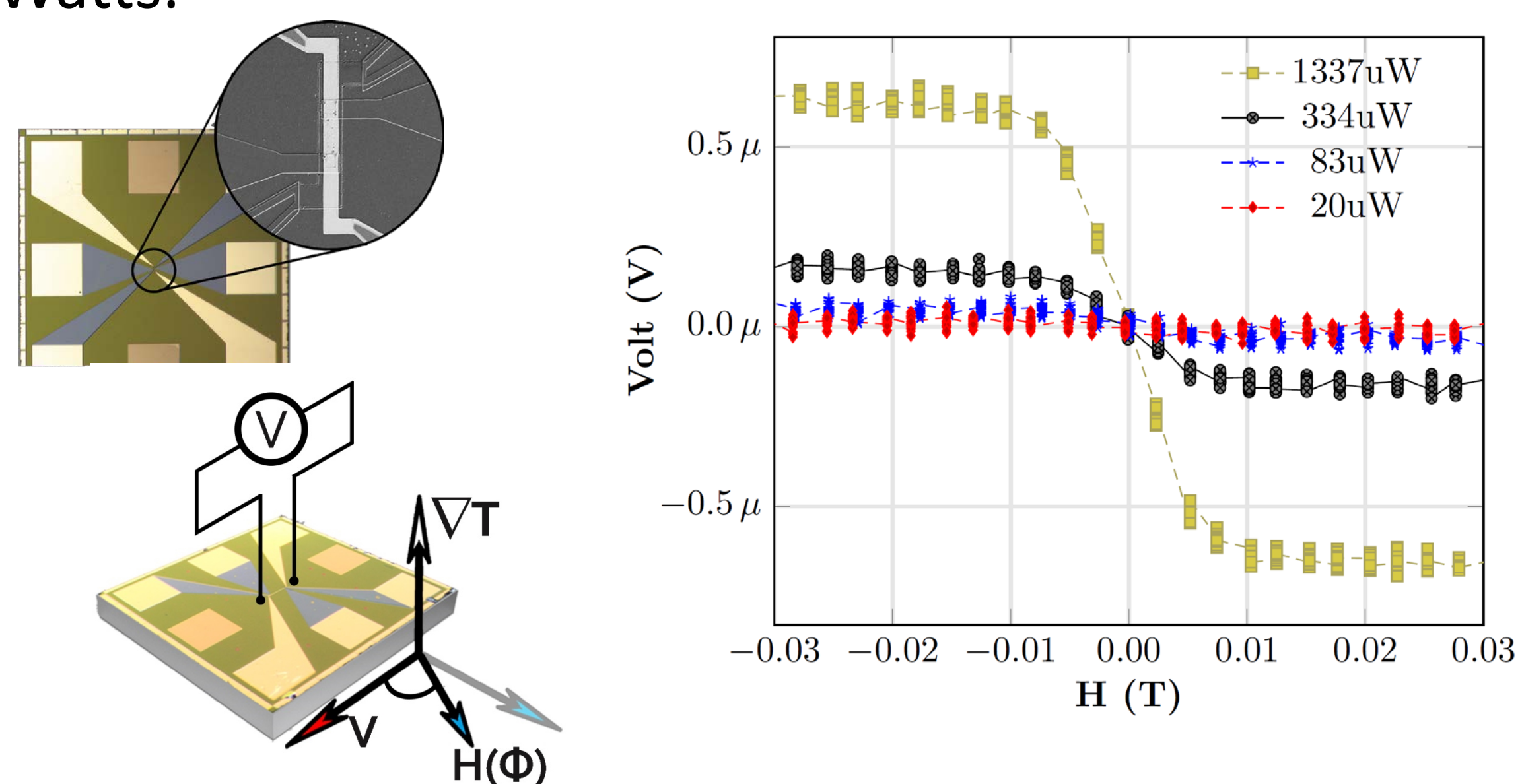
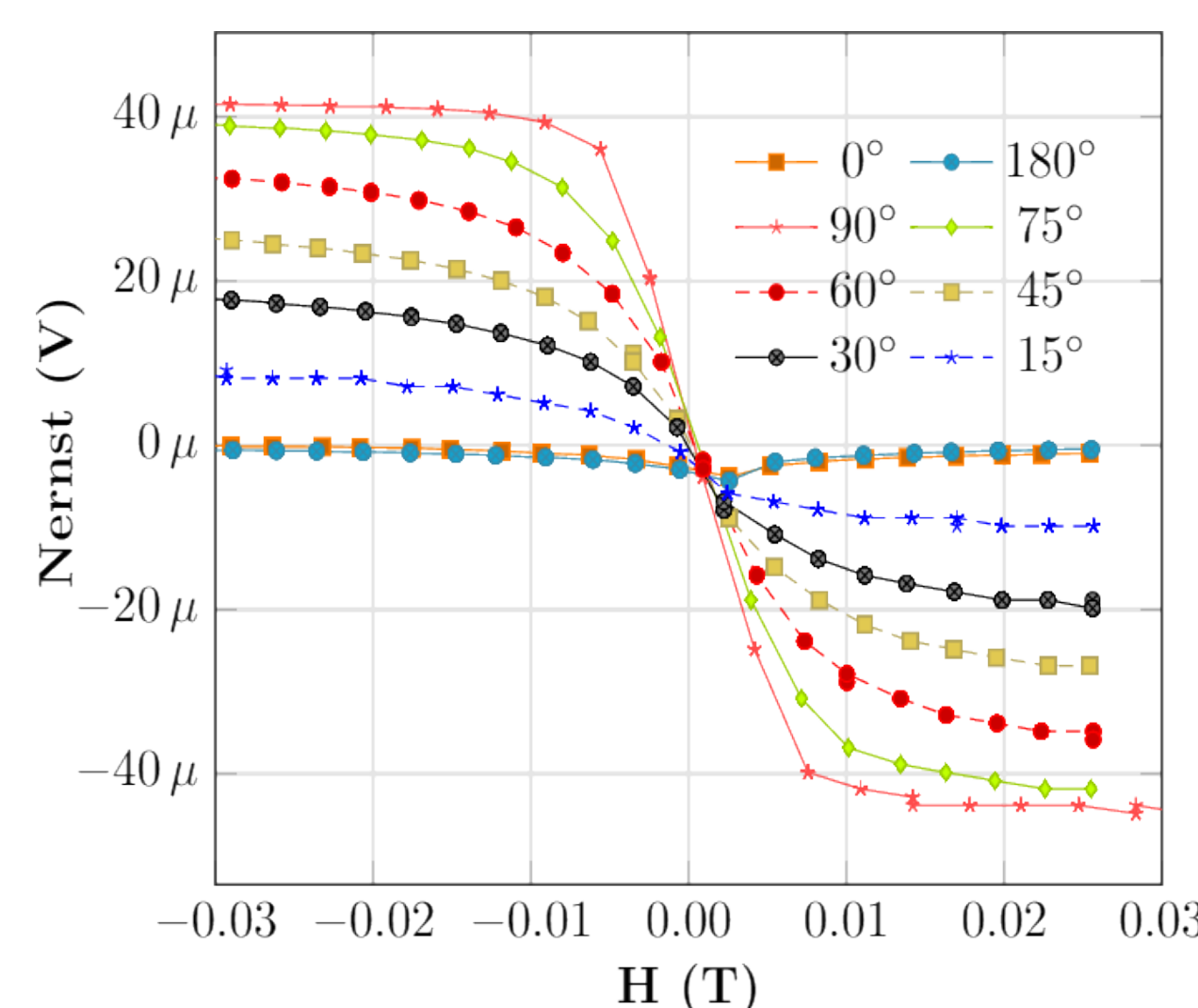


Figure 1: Fast response to an stimulus of 362 microWatts

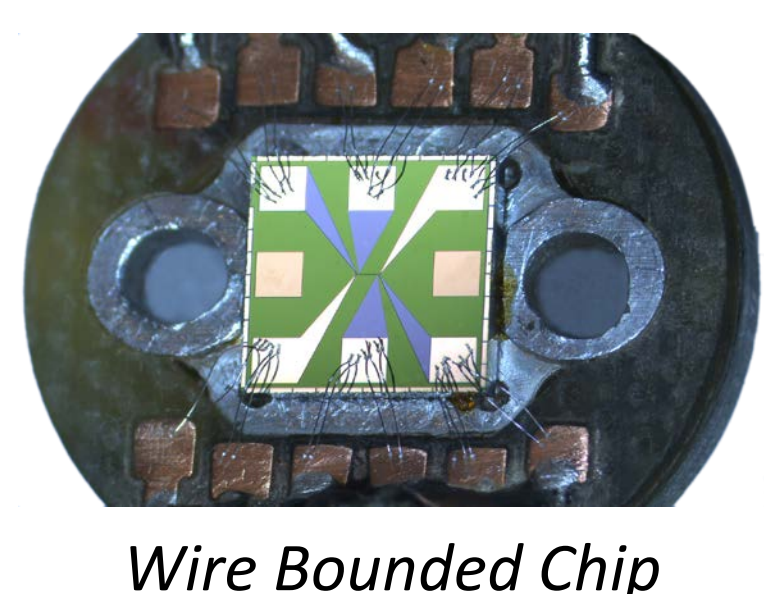
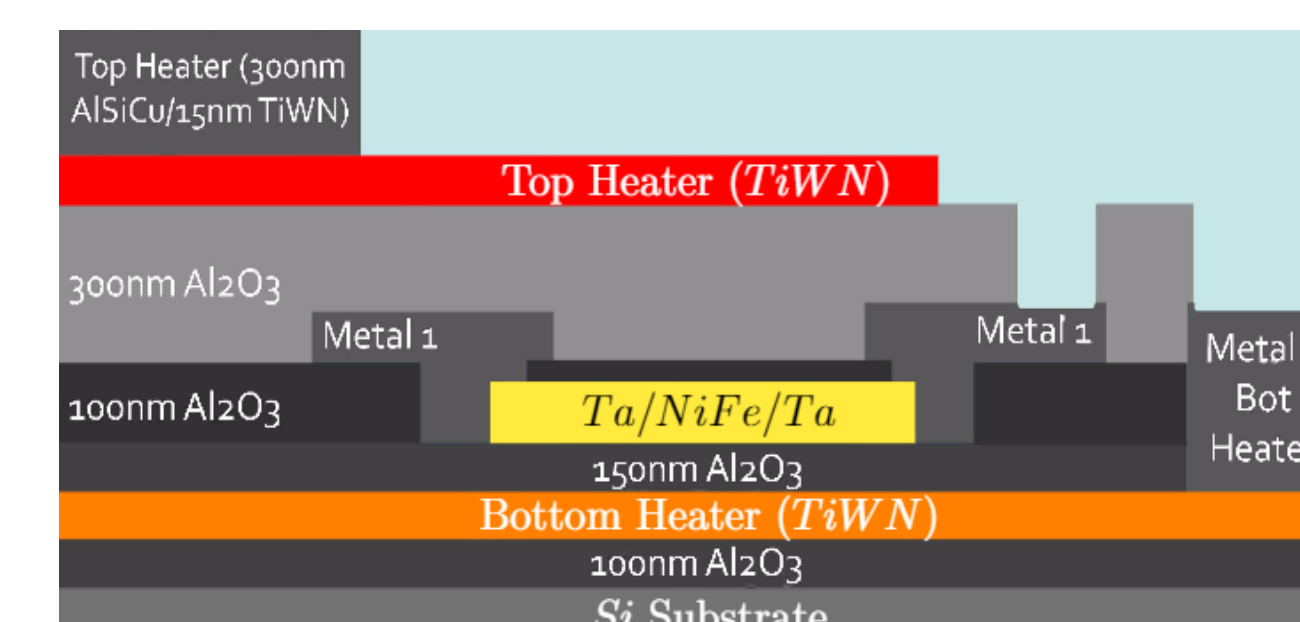
**Nernst voltage vs power.** Response under constant power values while changing the field. The minimum detectable power dissipation using the multi line device is in the order of tens of microWatts.



**Nernst voltage vs field orientation.** The power dissipated remains constant while we change the field values from -30mT to 30mT and the field orientation.  $E_{ANE} = Q_s \mu_0 (M \times \nabla T)$



Internal Device structure:  
layers of materials and dimensions.



Wire Bounded Chip

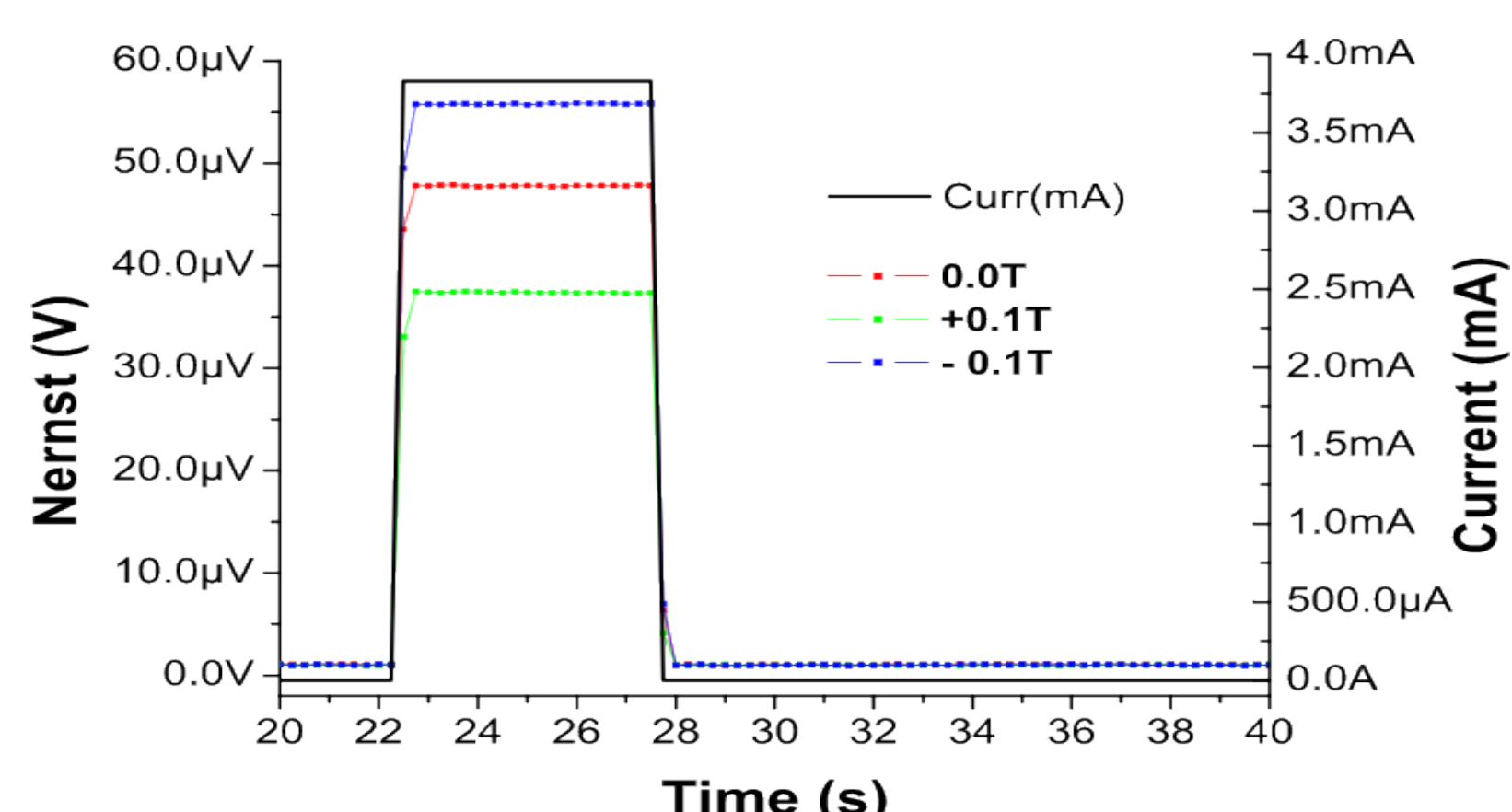


Figure 2: Nernst voltage vs. time, under a pulse of 20 mW power dissipated using the top heater.